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Inventor: Ji Ung Lee et al.

Title: "Field Effect Transistor Fabrication Methods, Field Emission Device Fabrication Methods, and Field Emission Device Operational Methods"

Assignee: Micron Technology, Inc.

PTO
JC9968 S. PTO
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02/05/02

EL 844054097

INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a continuation application of co-pending application Serial No. 09/260,231, filed March 1, 1999. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. § 1.98(d) and MPEP § 609(2).

Citation of these references is respectfully requested.

Respectfully submitted,

Dated: 2/5/02

By: [Signature]
James D. Shaurette
Reg. No. 39,833

Form PTO-1449

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Ji Ung Lee et al.FILING DATE
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U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclasses	Filing Date If Appropriate
	AA	5,482,870	01/09/96	Inoue			
	AB	5,372,973	12/13/94	Doan et al.			
	AC	5,229,331	07/20/93	Doan et al.			
	AD	5,210,472	05/11/93	Casper et al.			
	AE	4,988,638	01/29/91	Huang et al.			
	AF	6,057,555	5/2/00	Reedy et al.			
	AG	5,710,478	1/20/98	Kanemaru et a.			
	AH	6,020,683	2/1/00	Cathey, Jr. et al.			
	AI	6,249,327 B1	6/19/01	Murade et al.			
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclasses	Translation	
							Yes	No
	AL	5-114734	05/07/93	Japan			X	
	AM	3-194937	08/26/91	Japan			X	
	AN	3-159250	07/09/91	Japan			X	
	AO	A-2-143462	11/24/88	Japan			X	
	AP	61-252667	11/10/86	Japan			X	
	AQ	A-57-85262	11/17/80	Japan			X	

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AR		Polycrystalline Silicon Thin Film Transistor Incorporating a Semi-Insulating Field Plate for High Voltage Circuitry on Glass,
			F.J. Clough, E.M.S. Narayanan, Y. Chen, W. Eccleston, and W.I. Mäne, Appl. Phys. Lett. 71 - 10/08/97, pages 2002-2004, 1997 American Institute of Physics.
	AS		Geometry Dependence of the Transport Parameters in Field Effect Transistors Made From Amorphous Silicon, S. Griep, Mat. Res. Soc. Symp. Proc. 149,
			pages 283-288, 1989 Materials Research Society.
	AT		

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.